



## Bias Resistor Transistors

NPN Silicon Surface Mount Transistors with Monolithic

Bias Resistor Network

### FEATURES

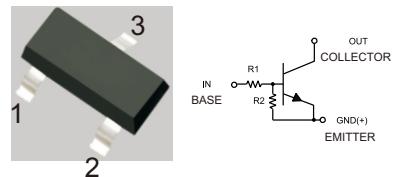
- Reduces board space
- Simplifies Circuit Design
- Reduces Board Space and Component Count

### Mechanical Data

- Case: SOT-23
- $R_1 = 22K\Omega$  (Typ) ,  $R_2 = 47K\Omega$  (Typ)

### PINNING

PIN	DESCRIPTION
1	BASE
2	EMITTER
3	COLLECTOR



Simplified outline SOT-23 and symbol

### MAXIMUM RATINGS (Ta = 25°C unless otherwise noted)

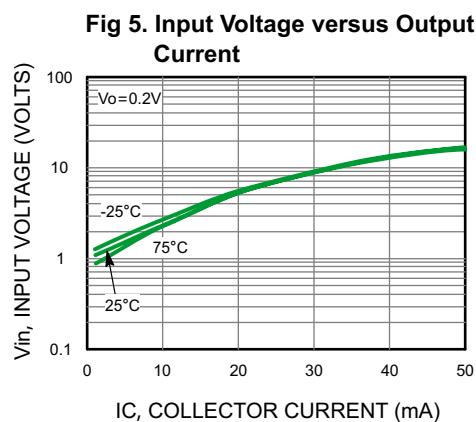
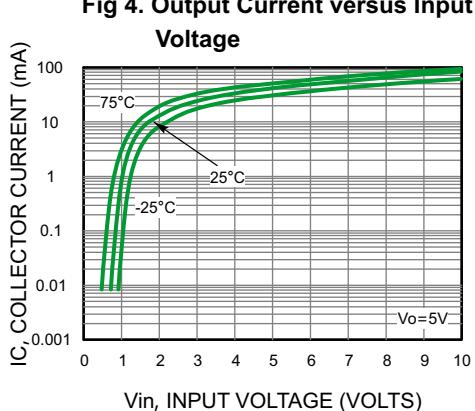
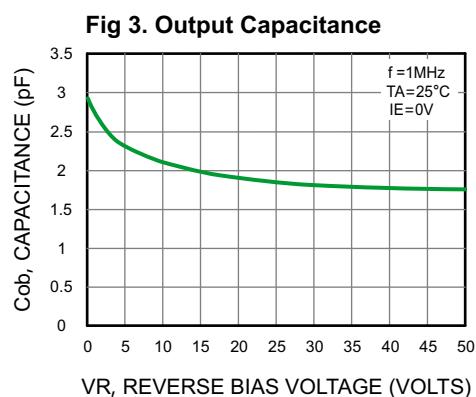
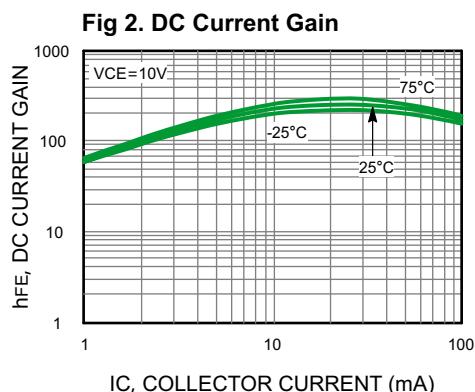
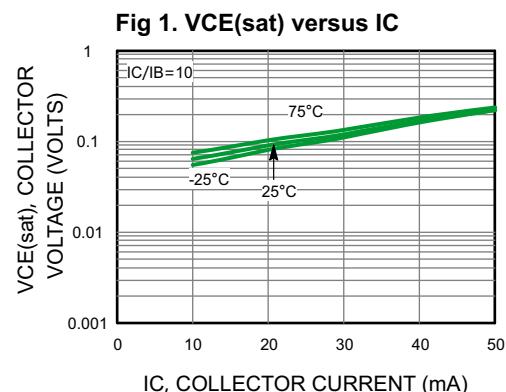
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	50	V
Output current	I <sub>C</sub>	100	mA
Power dissipation	P <sub>D</sub>	200	mW
Thermal Resistance – Junction-to-Ambient	R <sub>θJA</sub>	625	°C/W
Junction temperature	T <sub>J</sub>	150	°C
Range of storage temperature	T <sub>stg</sub>	-55~ +150	°C

### ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted. )

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10uA , I <sub>E</sub> = 0	50			V
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 2mA , I <sub>B</sub> = 0	50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 1mA , I <sub>C</sub> = 0	7			V
Collector-Base Cut off Current	I <sub>CBO</sub>	V <sub>CB</sub> = 50V , I <sub>E</sub> = 0			100	nA
Collector-Emitter Cut off Current	I <sub>CEO</sub>	V <sub>CE</sub> = 50V , I <sub>B</sub> = 0			0.5	uA
Emitter-Base Cut off Current	I <sub>EBO</sub>	V <sub>EB</sub> = 6V , I <sub>C</sub> = 0			0.13	mA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 10V , I <sub>C</sub> = 5mA	80			
Output Voltage (on)	V <sub>OL</sub>	V <sub>CE</sub> = 5.0V , V <sub>BE</sub> = 2.5V , R <sub>L</sub> = 1.0KΩ			0.2	V
Output Voltage (off)	V <sub>OH</sub>	V <sub>CE</sub> = 5.0V , V <sub>BE</sub> = 0.5V , R <sub>L</sub> = 1.0KΩ	4.9			V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 10mA , I <sub>B</sub> = 1mA			0.25	V
Input Voltage(off)	V <sub>I(off)</sub>	V <sub>CE</sub> = 5V , I <sub>C</sub> = 100μA	0.5			V
Input Voltage(on)	V <sub>I(on)</sub>	V <sub>CE</sub> = 0.3V , I <sub>C</sub> = 2mA			2	V
Input resistance	R <sub>1</sub>		15.4	22.0	28.6	KΩ
Input resistance	R <sub>2</sub>		32.9	47.0	61.1	KΩ
Resistance ratio	R <sub>2</sub> / R <sub>1</sub>		1.7	2.1	2.6	

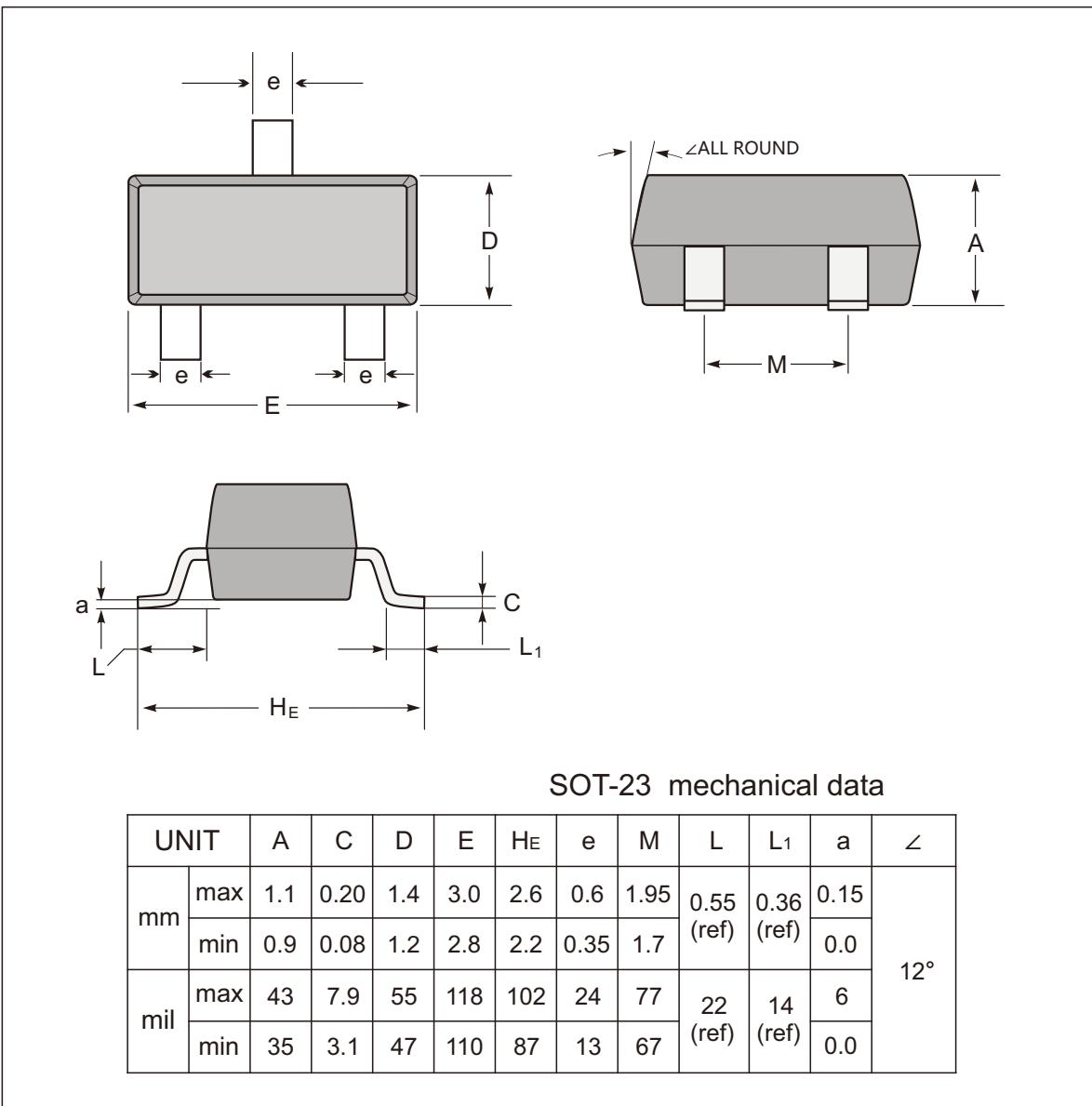


### Typical Performance Characteristics

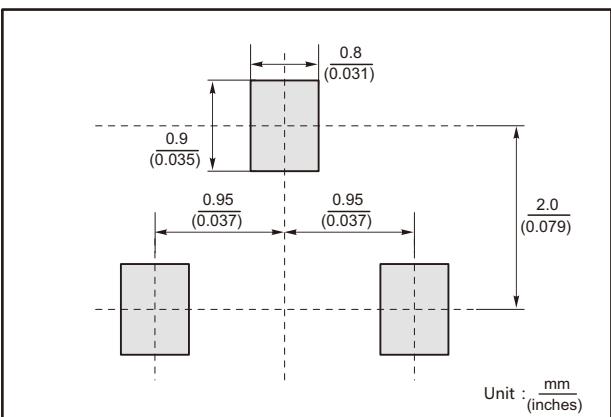




### SOT-23 Package Outline Dimensions



#### The recommended mounting pad size



#### Marking

Type number	Marking code
JDTC124XWD	24X



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